BLM7G22S-60PB; BLM7G22S-60PBG

AMPLEON

LDMOS 2-stage power MMIC

Rev. 5 — 1 September 2015 **Product data sheet**

1. Product profile

1.1 General description

The BLM7G22S-60PB(G) is a dual path, 2-stage power MMIC using Ampleon's state of the art GEN7 LDMOS technology. This device is perfectly suited as general purpose driver in the frequency range from 2100 MHz to 2400 MHz. Available in gull wing or flat lead outline.

Table 1. Application performance

Typical RF performance at T_{case} = 25 °C; I_{Dq1} = 75 mA; I_{Dq2} = 233 mA.
Test signal: 3GPP test model 1; 64 DPCH; clipping at 46 %; PAR = 8.4 dB at 0.01% probability on CCDF per carrier; carrier spacing = 5 MHz; per section unless otherwise specified in a class-AB production circuit.

Test signal	f	V_{DS}	$P_{L(AV)}$	G_p	η_D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2140	28	1.6	31.5	11.3	–43
2-carrier W-CDMA	2350	28	1.6	29.3	10.7	–42

1.2 Features and benefits

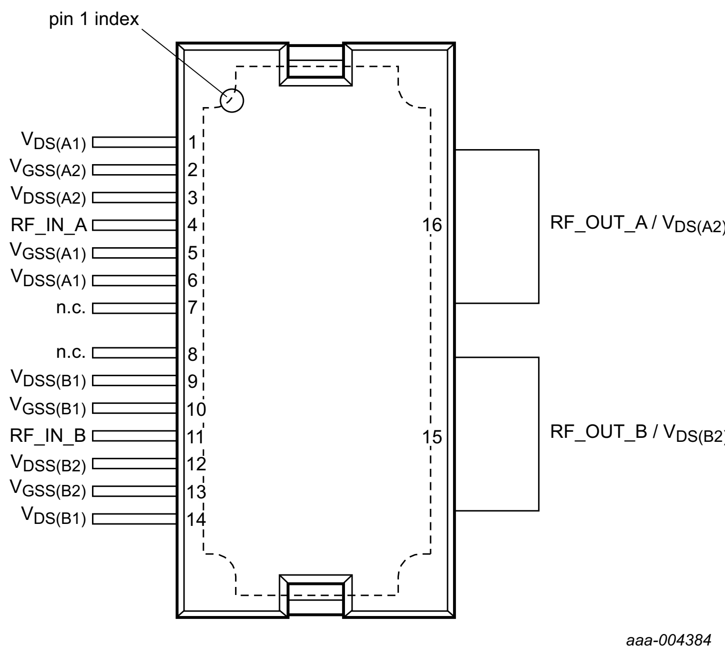
- Integrated temperature compensated bias
- Biasing of individual stages is externally accessible
- Integrated current sense
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- On-chip matching for ease of use (input matched to 50 Ω; output partially matched)
- Designed for broadband operation (frequency 2100 MHz to 2400 MHz)
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

RF power MMIC for W-CDMA base stations in the 2100 MHz to 2400 MHz frequency range.

2. Pinning information

2.1 Pinning



Transparent top view

The exposed backside of the package is the ground terminal of the device.

Fig 1. Pin configuration

2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$V_{DS(A1)}$	1	drain-source voltage of stage A1
$V_{GSS(A2)}$	2	gate sense FET and gate source voltage of stage A2
$V_{DSS(A2)}$	3	drain sense FET source voltage of stage A2
RF_IN_A	4	RF input path A
$V_{GSS(A1)}$	5	gate sense FET and gate source voltage of stage A1
$V_{DSS(A1)}$	6	drain sense FET source voltage of stage A1
n.c.	7	not connected
n.c.	8	not connected
$V_{DSS(B1)}$	9	drain sense FET source voltage of stage B1
$V_{GSS(B1)}$	10	gate sense FET and gate source voltage of stage B1
RF_IN_B	11	RF input path of B
$V_{DSS(B2)}$	12	drain sense FET source voltage of stage B2
$V_{GSS(B2)}$	13	gate sense FET and gate source voltage of stage B2
$V_{DS(B1)}$	14	drain-source voltage of stage B1

Table 2. Pin description *...continued*

Symbol	Pin	Description
RF_OUT_B/$V_{DS(B2)}$	15	RF output path B / drain source voltage of stage B2
RF_OUT_A/$V_{DS(A2)}$	16	RF output path A / drain source voltage of stage A2
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLM7G22S-60PB	HSOP16F	plastic, heatsink small outline package; 16 leads (flat)	SOT1211-2
BLM7G22S-60PBG	HSOP16	plastic, heatsink small outline package; 16 leads	SOT1212-2

4. Block diagram

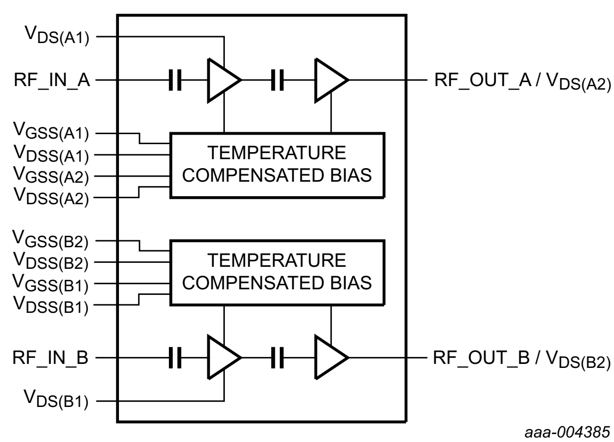


Fig 2. Block diagram of BLM7G22-60PBG

5. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		−0.5	+13	V
$V_{GS(sense)}$	sense gate-source voltage		−0.5	+9	V
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature	[1]	-	225	°C
T_{case}	case temperature		-	150	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics
Measured for total device.

Symbol	Parameter	Conditions	Value	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	final stage; T_{case} = 90 °C; P_L = 3.2 W [1]	1.1	K/W
		driver stage; T_{case} = 90 °C; P_L = 3.2 W [1]	3.2	K/W

[1] When operated with a CW signal.

7. Characteristics

Table 6. DC characteristics
T_{case} = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Final stage						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.422 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 42 mA	1.4	1.9	2.4	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 253 mA	1.7	2.1	2.5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	μA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	7.8	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 1478 mA	-	2.85	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 1.48 A	-	350	-	mΩ
I_{Dq}	quiescent drain current	main transistor: V_{DS} = 28 V sense transistor: I_D = 7 mA; V_{DS} = 28 V	208	233	257	mA
Driver stage						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.116 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 11.6 mA	1.4	1.9	2.4	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 69.6 mA	1.7	2.1	2.5	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	μA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	2.2	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 406 mA	-	0.8	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 0.4 A	-	2350	-	mΩ
I_{Dq}	quiescent drain current	main transistor: V_{DS} = 28 V sense transistor: I_D = 7 mA; V_{DS} = 28 V	67	75	83	mA

Table 7. RF Characteristics

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = 75 mA; I_{Dq2} = 233 mA. Test signal: 2-carrier W-CDMA; 3GPP test model 1; 64 DPCH; clipping at 46 %; PAR = 8.4 dB at 0.01% probability on CCDF per carrier; carrier spacing = 5 MHz; f = 2140 MHz; per section unless otherwise specified, measured in a class-AB production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)}$ = 1.6 W	29.5	31.5	33.5	dB
η_D	drain efficiency	$P_{L(AV)}$ = 1.6 W	10	11.3	-	%
RL_{in}	input return loss	$P_{L(AV)}$ = 1.6 W	-	−17	−10	dB
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 1.6 W	-	−43	−40	dBc

8. Application information

8.1 Circuit information for application circuit (2.1 GHz to 2.2 GHz)

Table 8. List of components

For test circuit see Figure 3.

Component	Description	Value	Remarks
C1, C4, C21, C24, C100, C200, C300, C400	capacitor	10 μF	
C2, C5, C6, C22, C25, C26	capacitor	1 μF	
C3, C7, C10, C23, C27, C30	capacitor	8.2 pF [1]	
C8, C28	capacitor	1.6 pF [1]	
C9, C29	capacitor	0.4 pF [1]	
C11, C31	electrolytic capacitor	470 μF	
C101, C201, C301, C401	capacitor	100 nF	
C102, C103, C105, C202, C203, C205, C302, C303, C305, C402, C403, C405	capacitor	12 pF [2]	
C104, C204, C304, C404	capacitor	4.7 μF	
D100, D200, D300, D400	IC: LM4051	-	
P100, P400	potentiometer	-	do not populate
Q100, Q200, Q300, Q400	IC: LM7341	-	
R1, R21	ferrite bead	-	
R100, R200, R300, R400	resistor	4.7 Ω	
R101, R108, R208, R308, R401, R408	resistor	0 Ω	
R102, R402	resistor	360 Ω	1% tolerance
R103, R403	resistor	330 Ω	1% tolerance
R104, R203, R303, R404	resistor	68 kΩ	
R105, R405	resistor	10 kΩ	
R106, R205, R305, R406	resistor	820 Ω	
R107, R206, R306, R407	resistor	47 Ω	
R109, R209, R309, R409	resistor	300 kΩ	
R201, R301	resistor	180 Ω	1% tolerance

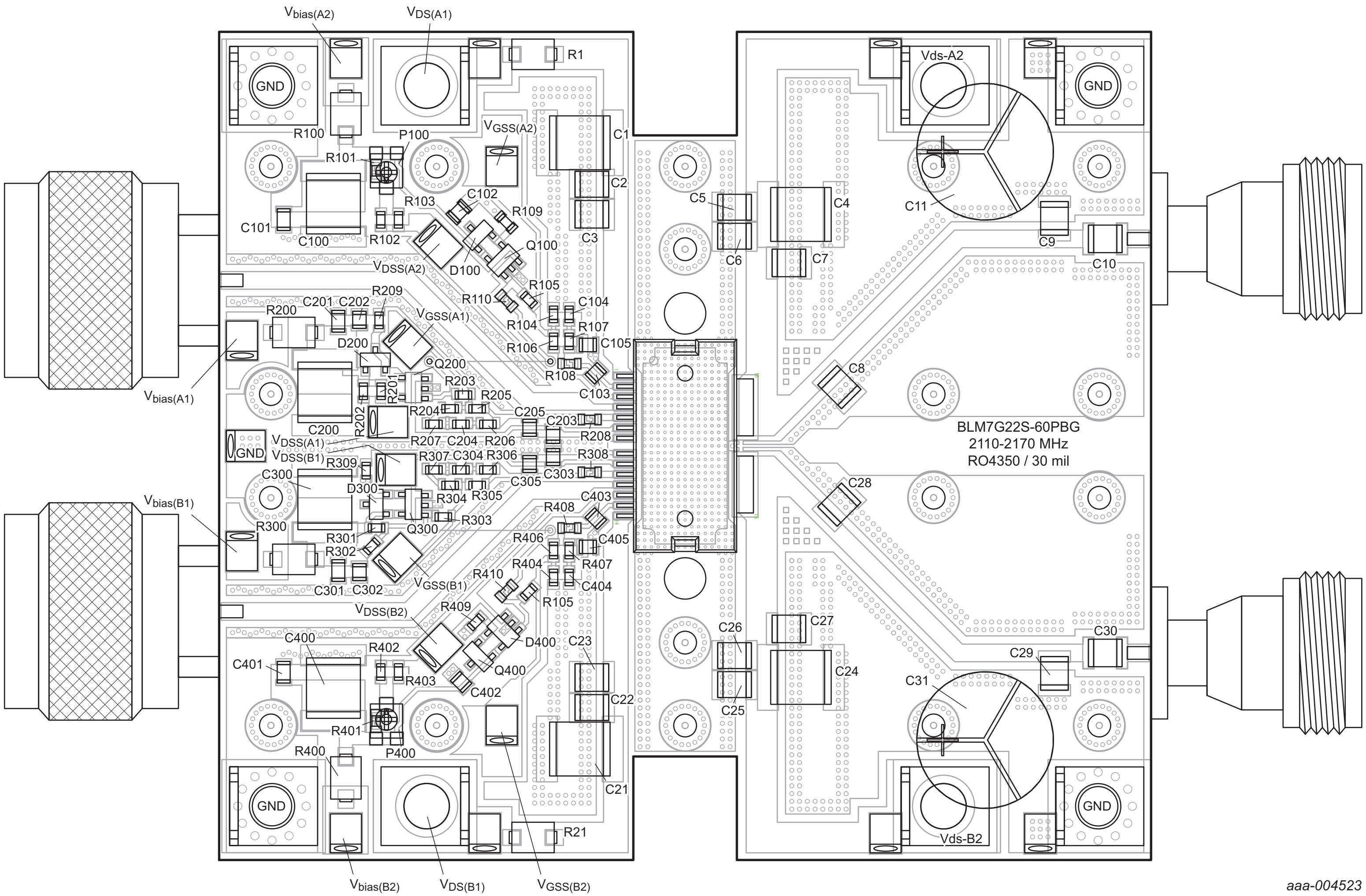
Table 8. List of components *...continued*

For test circuit see Figure 3.

Component	Description	Value	Remarks
R202, R302	resistor	3.6 kΩ	1% tolerance
R204, R304	resistor	9.1 kΩ	
R207, R307	resistor	1 kΩ	

[1] American Technical Ceramics type 100B or capacitor of same quality.

[2] American Technical Ceramics type 100A or capacitor of same quality.



Printed-Circuit Board (PCB): Rogers 4350; thickness = 0.762 mm.

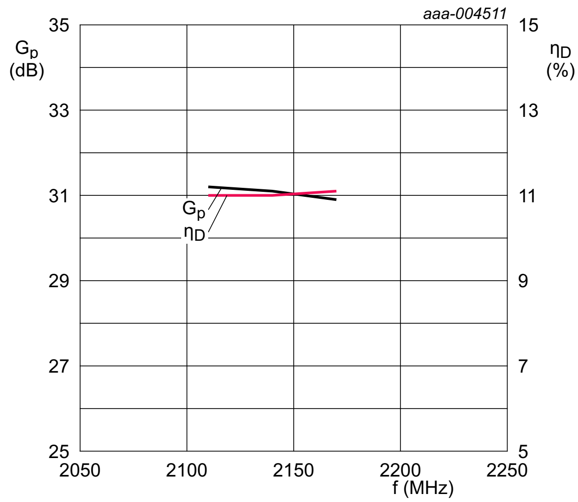
See Table 8 for a list of components.

Fig 3. Component layout for class-AB application circuit with auto-bias

8.2 Performance curves (2.1 GHz to 2.2 GHz)

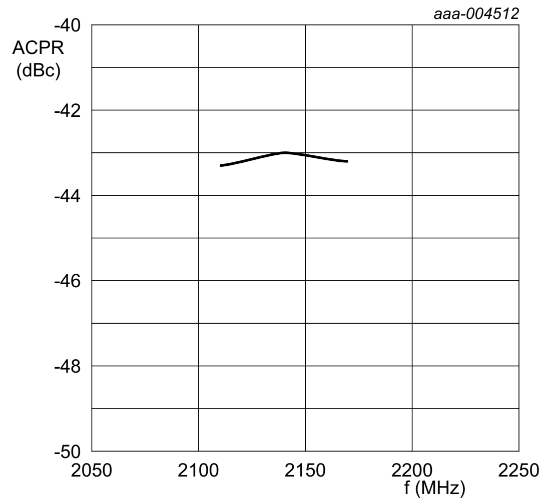
Performance curves are measured in a class-AB dedicated application circuit with auto-bias from 2.1 GHz to 2.2 GHz, see Table 8 and Figure 3.

8.2.1 W-CDMA



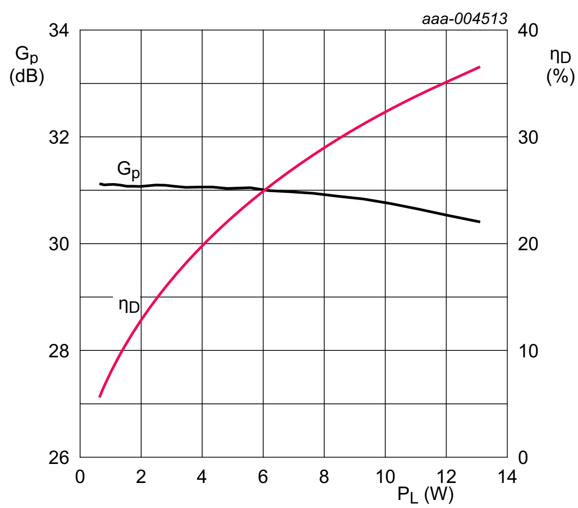
T_{case} = 25 °C; V_{DS} = 28 V; $P_{L(AV)}$ = 1.6 W; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; carrier spacing = 5 MHz.

Fig 4. Power gain and drain efficiency as function of frequency; typical values



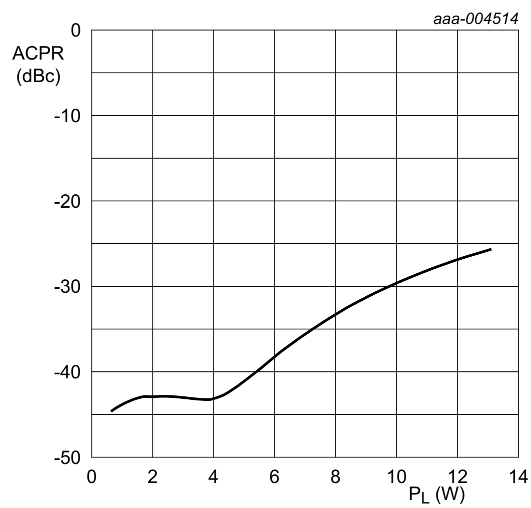
T_{case} = 25 °C; V_{DS} = 28 V; $P_{L(AV)}$ = 1.6 W; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; carrier spacing = 5 MHz.

Fig 5. Adjacent channel power ratio as a function of frequency; typical values



T_{case} = 25 °C; V_{DS} = 28 V; f = 2140 MHz; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; carrier spacing = 5 MHz.

Fig 6. Power gain and drain efficiency as function of output power; typical values



T_{case} = 25 °C; V_{DS} = 28 V; f = 2140 MHz; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; carrier spacing = 5 MHz.

Fig 7. Adjacent channel power ratio as a function of output power; typical values

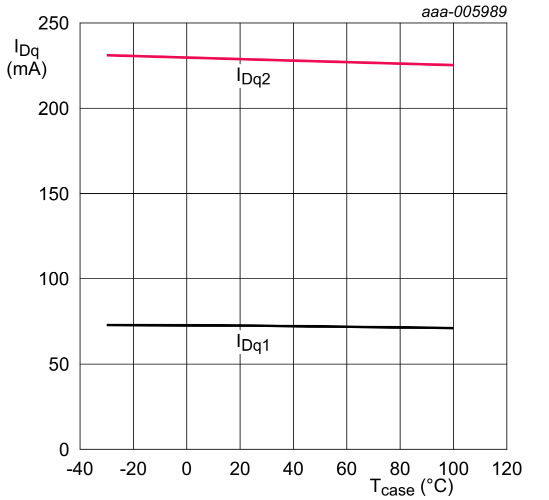
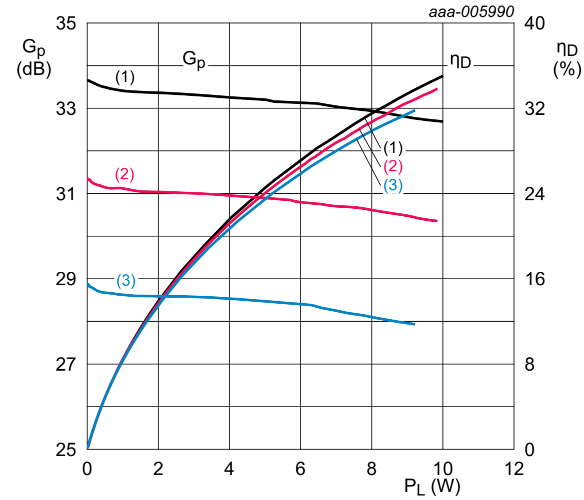


Fig 8. Quiescent drain current as a function of case temperature; typical values



V_{DS} = 28 V; f = 2140 MHz; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; carrier spacing = 5 MHz.

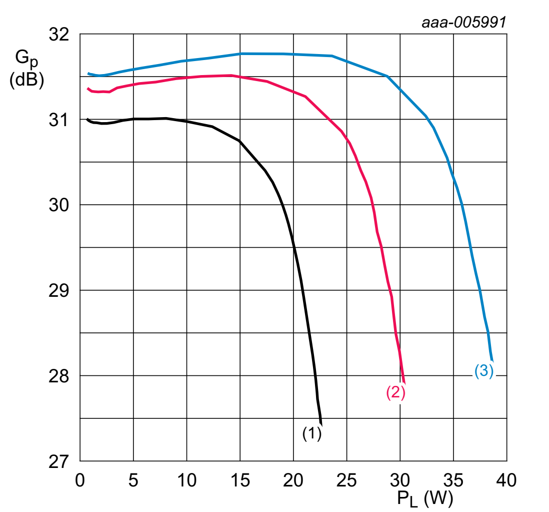
(1) T_{case} = −30 °C

(2) T_{case} = +25 °C

(3) T_{case} = +100 °C

Fig 9. Power gain and drain efficiency as function of output power; typical values

8.2.2 1-Tone pulsed CW



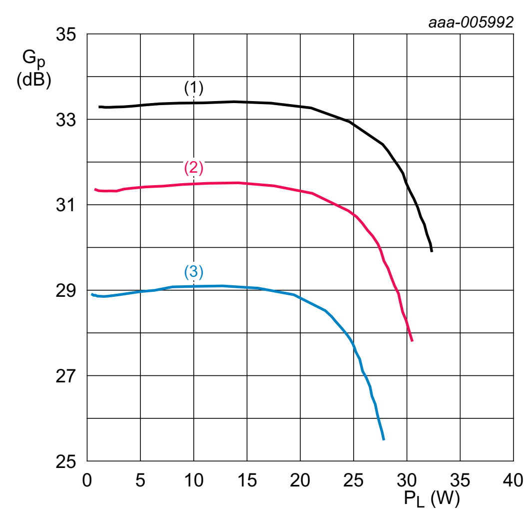
T_{case} = 25 °C; V_{DS} = 28 V; $P_{L(AV)}$ = 1.6 W; f = 2140 MHz; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; δ = 10 %; t_p = 100 μs.

(1) V_{DD} = 24 V

(2) V_{DD} = 28 V

(3) V_{DD} = 32 V

Fig 10. Power gain as a function of output power; typical values



V_{DS} = 28 V; $P_{L(AV)}$ = 1.6 W; f = 2140 MHz; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; δ = 10 %; t_p = 100 μs.

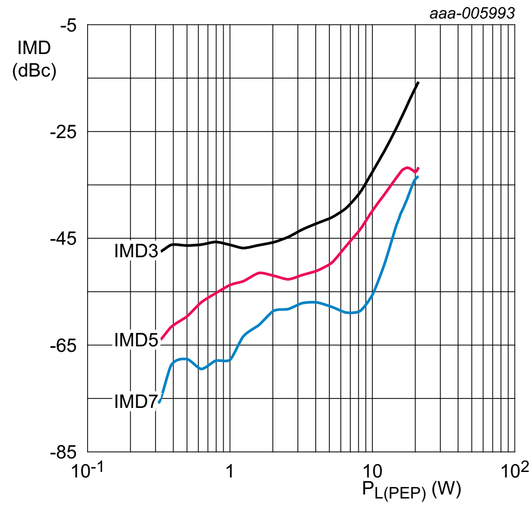
(1) T_{case} = −30 °C

(2) T_{case} = +25 °C

(3) T_{case} = +100 °C

Fig 11. Power gain as a function of output power; typical values

8.2.3 2-Tone CW



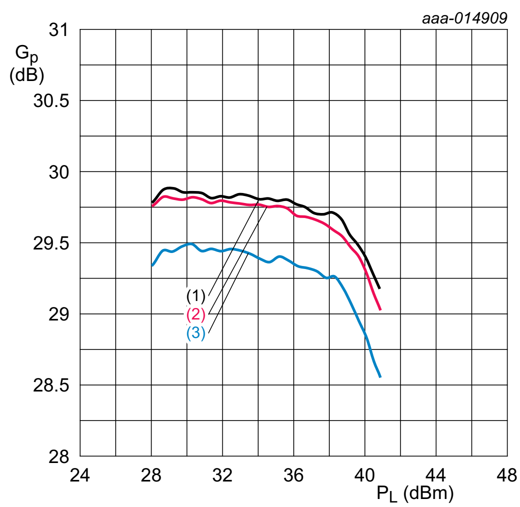
T_{case} = 25 °C; V_{DS} = 28 V; f_c = 2140 MHz; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; tone spacing = 100 kHz.

Fig 12. Intermodulation distortion as a function of peak envelope power load power; typical values

8.3 Performance curves (2.3 GHz to 2.4 GHz)

Performance curves are measured in a class-AB dedicated application circuit with auto-bias from 2.3 GHz to 2.4 GHz.

8.3.1 2-Carrier W-CDMA



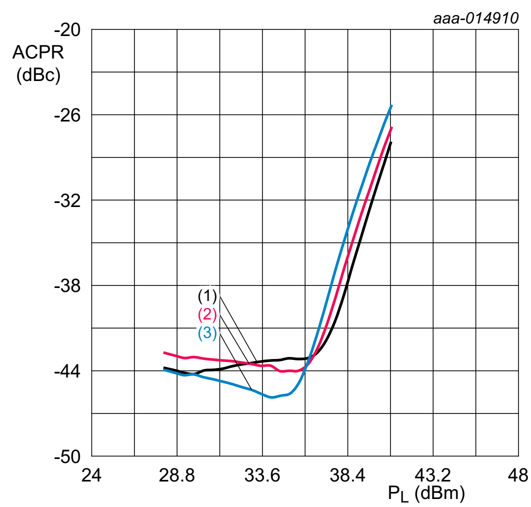
V_{DS} = 28 V; I_{Dq1} = 220 mA; I_{Dq2} = 75 mA; carrier spacing = 5MHz.

(1) f = 2300 MHz

(2) f = 2350 MHz

(3) f = 2400 MHz

Fig 13. Power gain as a function of output power; typical values



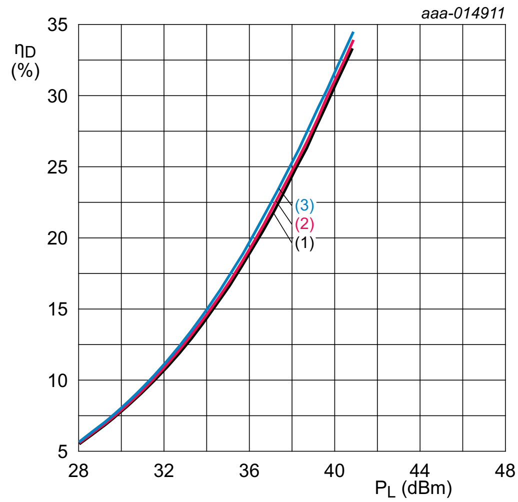
V_{DS} = 28 V; I_{Dq1} = 220 mA; I_{Dq2} = 75 mA; carrier spacing = 5MHz.

(1) f = 2300 MHz

(2) f = 2350 MHz

(3) f = 2400 MHz

Fig 14. Adjacent channel power ratio as a function of output power; typical values



V_{DS} = 28 V; I_{Dq1} = 220 mA; I_{Dq2} = 75 mA; carrier spacing = 5MHz.

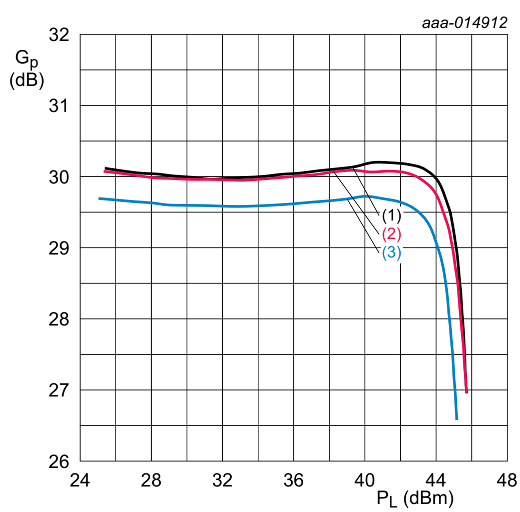
(1) f = 2300 MHz

(2) f = 2350 MHz

(3) f = 2400 MHz

Fig 15. Drain efficiency as a function of output power; typical values

8.3.2 Pulsed CW



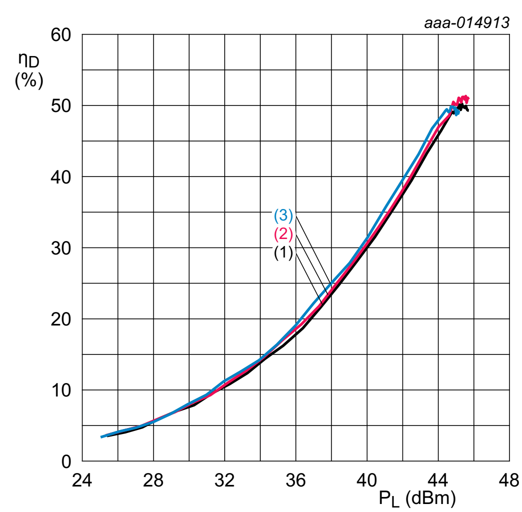
V_{DS} = 28 V; I_{Dq1} = 220 mA; I_{Dq2} = 75 mA; δ = 10 %; t_p = 100 μs.

(1) f = 2300 MHz

(2) f = 2350 MHz

(3) f = 2400 MHz

Fig 16. Power gain as a function of output power; typical values



V_{DS} = 28 V; I_{Dq1} = 220 mA; I_{Dq2} = 75 mA; δ = 10 %; t_p = 100 μs.

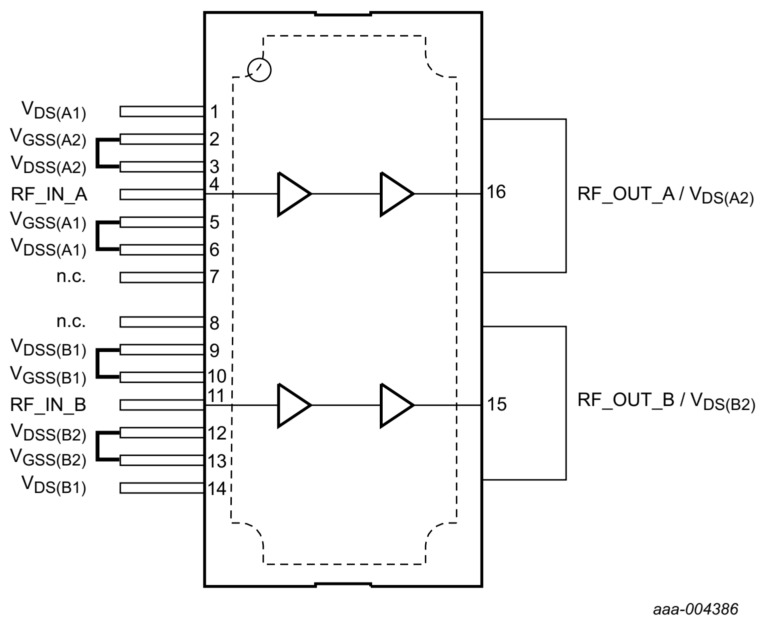
(1) f = 2300 MHz

(2) f = 2350 MHz

(3) f = 2400 MHz

Fig 17. Drain efficiency as a function of output power; typical values

8.4 Application without auto-bias



Connect pins 2 and 3; connect pins 5 and 6; connect pins 9 and 10; connect pins 12 and 13 at board level. The exposed backside of the package is the ground terminal of the device.

Fig 18. Non auto-bias application

9. Test information

9.1 Ruggedness

The BLM7G22S-60PB and BLM7G22S-60PBG are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq1} = 75 mA; I_{Dq2} = 233 mA; P_L = 27 W (W-CDMA); f = 2140 MHz.

9.2 Impedance information

Table 9. Typical impedance
Measured load-pull data. Typical values per section unless otherwise specified.

f	Z_S [1]	Z_L [1]
(MHz)	(Ω)	(Ω)
BLM7G22S-60PB		
2080	58.86 + j21.82	10.54 – j3.20
2110	58.70 + j29.76	10.23 – j2.72
2140	51.80 + j41.56	9.56 – j2.90
2170	47.31 + j44.60	9.10 – j2.80
2230	38.35 + j46.53	8.41 – j2.05
2300	30.80 + j53.60	6.40 – j2.10
2350	23.80 + j48.20	5.70 – j2.20
2400	19.10 + j43.20	5.30 – j2.40
BLM7G22S-60PBG		
2080	55.62 + j18.89	15.89 – j2.28
2110	55.61 + j19.04	14.74 – j2.59
2140	55.60 + j19.12	13.56 – j2.75
2170	55.57 + j19.25	12.38 – j2.75
2200	55.53 + j19.39	11.20 – j2.61
2230	55.48 + j19.55	10.05 – j2.34
2300	34.51 + j41.45	7.06 – j6.36
2350	29.26 + j36.91	6.35 – j6.24
2400	22.86 + j32.52	5.65 – j6.15

[1] Z_S and Z_L defined in Figure 19.

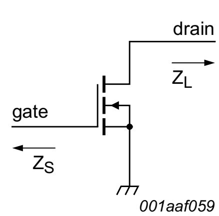
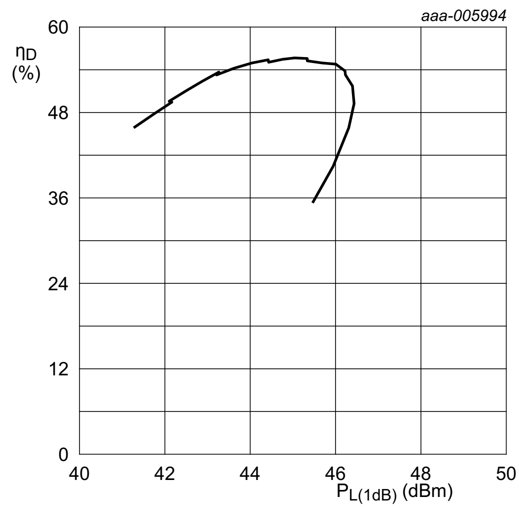


Fig 19. Definition of transistor impedance

9.3 Performance curves

Performance curves are measured per section.

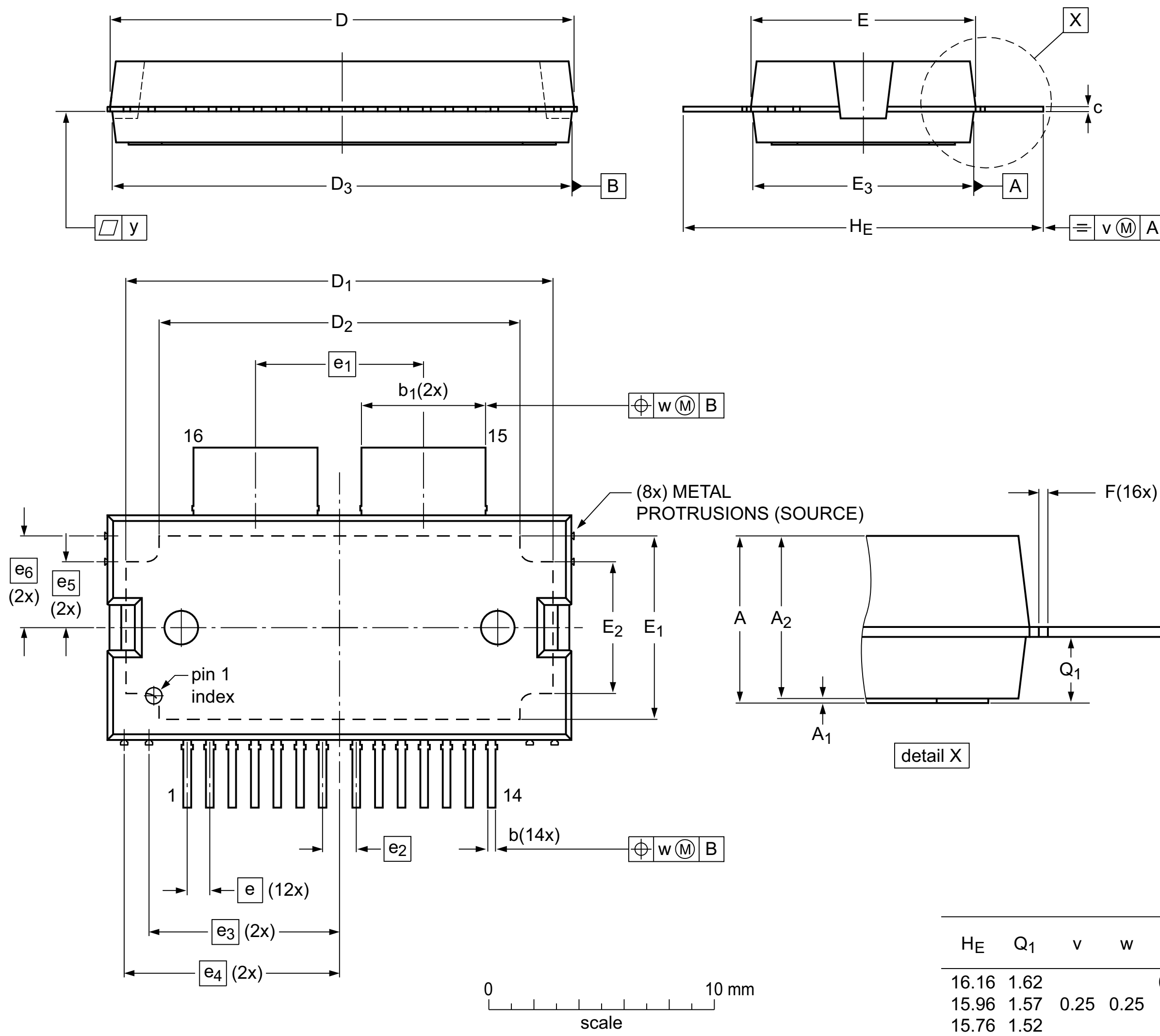


T_{case} = 25 °C; V_{DS} = 28 V; $P_{L(AV)}$ = 1.6 W; f = 2140 MHz; I_{Dq1} = 75 mA; I_{Dq2} = 232 mA; δ = 10 %; t_p = 100 μs.

Fig 20. One-tone pulsed CW drain efficiency at 1 dB gain compression as function of output power at 1 dB gain compression; typical values

10. Package outline

HSOP16F: plastic, heatsink small outline package; 16 leads(flat) **SOT1211-2**



H_E	Q_1	v	w	y
16.16	1.62			0.1
15.96	1.57	0.25	0.25	
15.76	1.52			

Dimensions (mm are the original dimensions)

Unit		A	A_1	A_2	b	b_1	c	D(1)	D_1	D_2	D_3	E(1)	E_1	E_2	E_3	e	e_1	e_2	e_3	e_4	e_5	e_6	F
mm	max	3.9	0.2	3.65	0.40	5.55	0.27	20.62	19.00	16.05	20.44	10.01	8.18	5.89	9.83								
	nom		0.1	3.60	0.35	5.50	0.22	20.57	18.95	16.00	20.39	9.96	8.13	5.84	9.78	1.0	7.45	1.5	8.45	9.55	2.97	4.07	0.2
	min		0	3.55	0.30	5.45	0.17	20.52	18.90	15.95	20.34	9.91	8.08	5.79	9.73								

Note

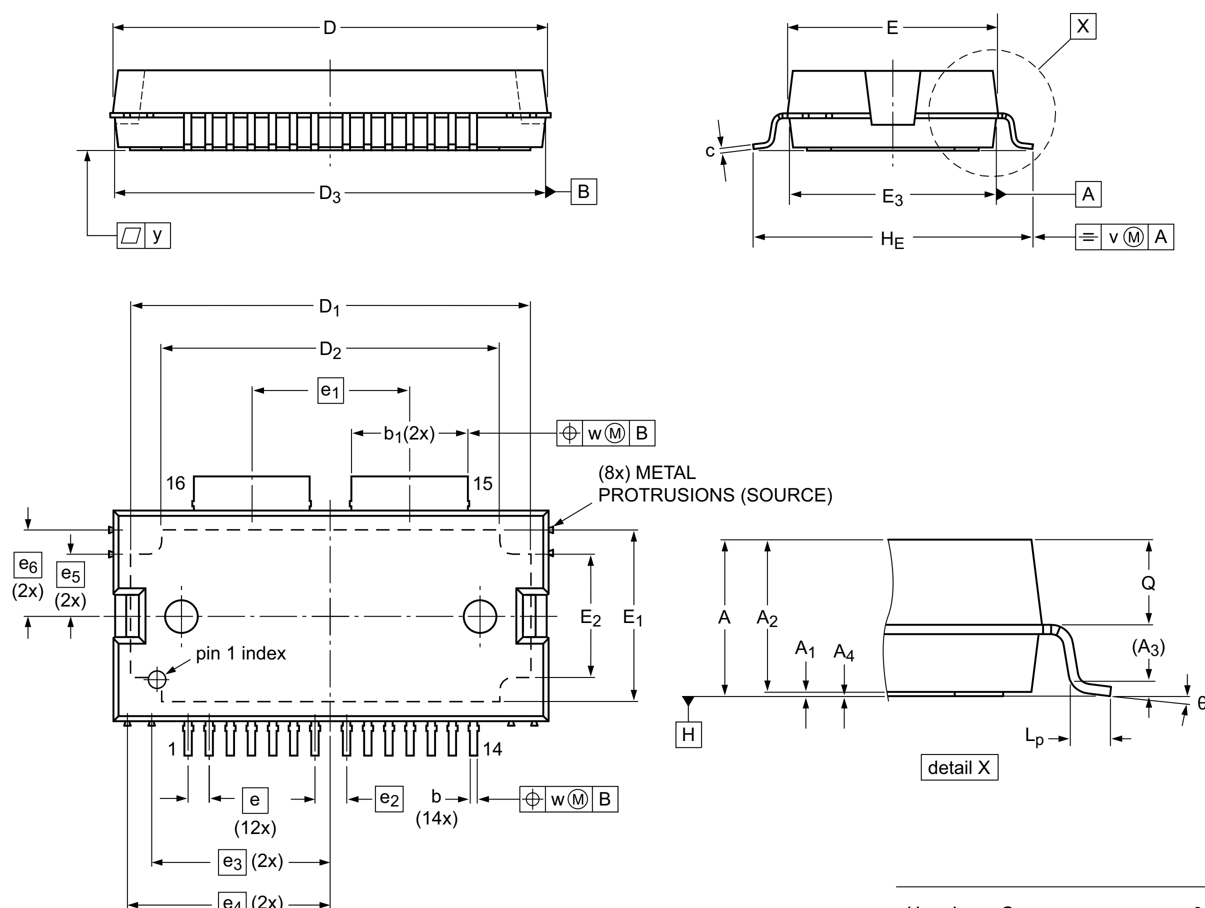
1. Package body dimensions “D and “E do not include mold and metal protrusions. Allowable protrusion is 0.25 mm per side.
2. Lead width dimensions “b and “ b_1 do not include dambar protrusions. Allowable dambar protrusion is 0.25 mm in total per lead.

sot1211-2_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1211-2						~~15-01-12~~ 15-06-09

Fig 21. Package outline SOT1211-2 (HSOP16F)

HSOP16: plastic, heatsink small outline package; 16 leads **SOT1212-2**



H_E	L_p	Q	v	w	y	θ
13.5	1.10	2.07			0.1	7°
13.2	0.95	2.02	0.25	0.25		3°
12.9	0.80	1.97				0°

0 10 mm
scale

Dimensions (mm are the original dimensions)

Unit		A	A_1	A_2	A_3	A_4	b	b_1	c	$D^{(1)}$	D_1	D_2	D_3	$E^{(1)}$	E_1	E_2	E_3	e	e_1	e_2	e_3	e_4	e_5	e_6
	max	3.9	0.2	3.65		0.06	0.40	5.55	0.27	20.62	19.00	16.05	20.44	10.01	8.18	5.89	9.83							
mm	nom		0.1	3.60	0.35	0	0.35	5.50	0.22	20.57	18.95	16.00	20.39	9.96	8.13	5.84	9.78	1.0	7.45	1.5	8.45	9.55	2.97	4.07
	min		0	3.55		-0.02	0.30	5.45	0.17	20.52	18.90	15.95	20.34	9.91	8.08	5.79	9.73							

Note
1. Package body dimensions “D" and `'E" do not include mold and metal protrusions. Allowable protrusion is 0.25 mm per side.
2. Lead width dimensions `'b" and `'b_1" do not include dambar protrusions. Allowable dambar protrusion is 0.25 mm in total per lead.
3. Dimension A_4 is measured with respect to bottom of the heatsink DATUM H. Positive value means that the bottom of the heatsink is higher than the bottom of the lead.

sot1212-2_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1212-2						~~15-01-14~~ 15-06-09

Fig 22. Package outline SOT1212-2 (HSOP16)

11. Handling information

CAUTION	
	This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices. Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

12. Abbreviations

Table 10. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Waveform
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
FET	Field-Effect Transistor
GEN7	Seventh Generation
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time To Failure
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

13. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM7G22S-60PB_7G22S-60PBG#5	20150901	Product data sheet		BLM7G22S-60PB_7G22S-60PBG v.4
Modifications:	• The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. • Legal texts have been adapted to the new company name where appropriate.			
BLM7G22S-60PB_7G22S-60PBG v.4	20150701	Product data sheet	-	BLM7G22S-60PB_7G22S-60PBG v.3
BLM7G22S-60PB_7G22S-60PBG v.3	20141016	Product data sheet	-	BLM7G22S-60PB_7G22S-60PBG v.2
BLM7G22S-60PB_7G22S-60PBG v.2	20140930	Product data sheet	-	BLM7G22S-60PB_7G22S-60PBG v.1
BLM7G22S-60PB_7G22S-60PBG v.1	20121211	Product data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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15. Contact information

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16. Contents

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